

FEATURES

- **High Current Transfer Ratio, 75% to 450%**
- **Minimum Current Transfer Ratio, 10%**
- **Guaranteed at $I_F=1.0\text{mA}$**
- **High Collector-Emitter Voltage, $BV_{CEO}=70\text{V}$**
- **Long Term Stability**
- **Industry Standard DIP Package**
- **Underwriters Lab File #E52744**
- **VDE 0884 Available with Option 1**

DESCRIPTION

The IL201/202/203 are optically coupled pairs employing a Gallium Arsenide infrared LED and a Silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output. The IL201/202/203 can be used to replace relays and transformers in many digital interface applications, as well as analog applications such as CRT modulation.

Maximum Ratings
Emitter

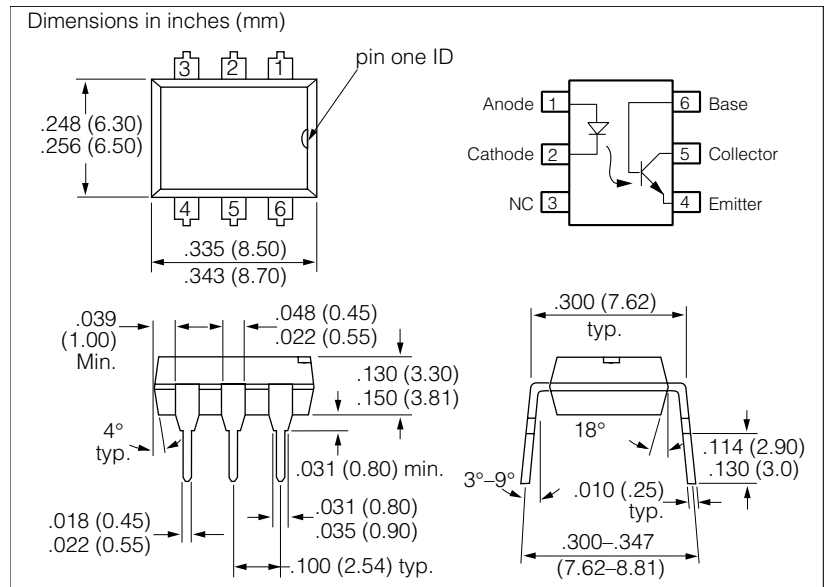
Peak Reverse Voltage 6.0 V
 Continuous Forward Current 60 mA
 Power Dissipation at 25°C 100 mW
 Derate Linearly from 25°C 1.33 mW/°C

Detector

Collector-Emitter Breakdown Voltage,
 BV_{CEO} 70 V
 Emitter-Collector Breakdown Voltage,
 BV_{ECO} 7.0 V
 Collector-Base Breakdown Voltage,
 BV_{CBO} 70 V
 Power Dissipation 200 mW
 Derate Linearly from 25°C 2.6 mW/°C

Package

Isolation Test Voltage ($t=1.0$ sec.) 5300 V_{RMS}
 Total Package Dissipation at 25°C A
 (LED + Detector) 250 mW
 Derate Linearly from 25°C 3.3 mW/°C
 Creepage ≥ 7.0 min
 Clearance ≥ 7.0 min
 Storage Temperature -55°C to +150°C
 Operating Temperature -55°C to +100°C
 Lead Soldering Time at 260°C 10 sec.


Characteristics 0°C to 70°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Emitter						
Forward Voltage	V_F	—	1.2	1.5	V	$I_F=20$ mA
Forward Voltage		—	1.0	1.2		$I_F=1.0$ mA
Breakdown Voltage		6.0	20	—		$I_R=10$ μ A
Reverse Current	I_R	—	0.1	10	μ A	$V_R=6.0$ V $T_A=25^\circ\text{C}$
Detector						
Transistor Gain	HFE	100	200	—	—	$V_{CE}=5.0$ V $I_C=100$ μ A
Breakdown Voltage Collector-Emitter	BV_{CEO}	70	—	—	V	$I_C=100$ μ A
Breakdown Voltage Emitter-Collector	BV_{ECO}	7.0	10	—		$I_E=100$ μ A
Breakdown Voltage Collector-Base	BV_{CBO}	70	90	—		$I_C=10$ μ A
Leakage Current Collector-Emitter	I_{CEO}	—	5.0	50	nA	$V_{CE}=10$ V, $T_A=25^\circ\text{C}$
Package						
Base Current Transfer Ratio	CTRCB	0.15	—	—	%	$I_F=10$ mA $V_{CB}=10$ V
	V_{CEsat}	—	—	0.4	V	$I_F=10$ mA $I_C=2.0$ mA
DC Current Transfer Ratio	CTR	IL201	75	100	150	% $I_F=10$ mA, $V_{CE}=10$ V
		IL202	125	200	250	
		IL203	225	300	450	
DC Current Transfer Ratio	CTR	IL201	10	—	—	% $I_F=1.0$ mA, $V_{CE}=10$ V
		IL202	30			
		IL203	50			

Figure 1. Forward voltage versus forward current

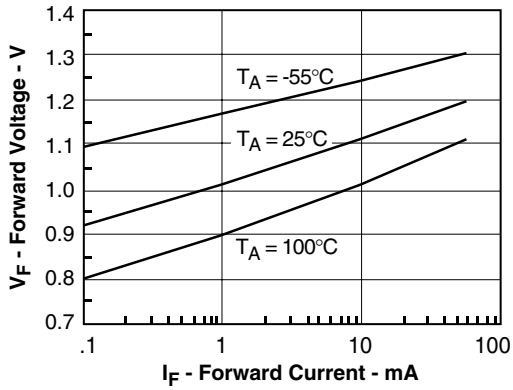


Figure 2. Normalized non-saturated and saturated CTR at $T_A=25^\circ\text{C}$ versus LED current

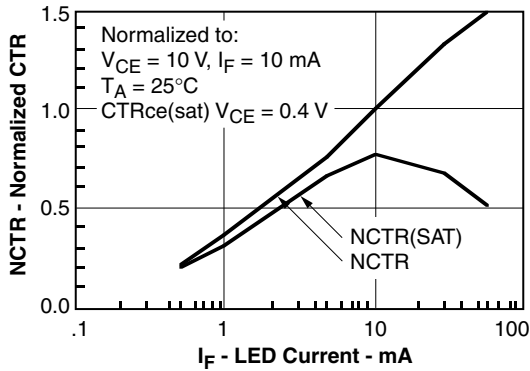


Figure 3. Normalized non-saturated and saturated CTR at $T_A=50^\circ\text{C}$ versus LED current

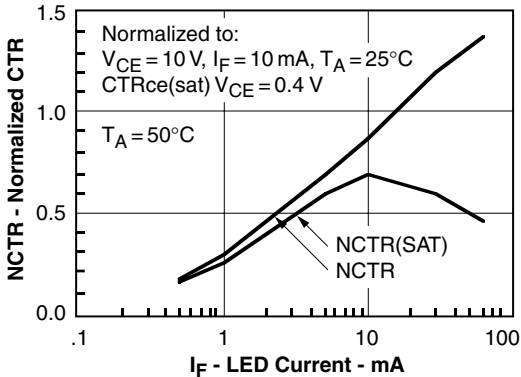


Figure 4. Normalized non-saturated and saturated CTR at $T_A=70^\circ\text{C}$ versus LED current

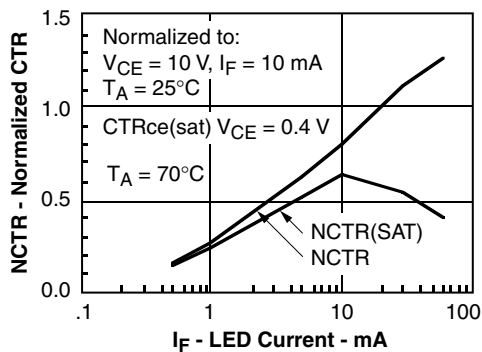


Figure 5. Normalized non-saturated and saturated CTR at $T_A=85^\circ\text{C}$ versus LED current

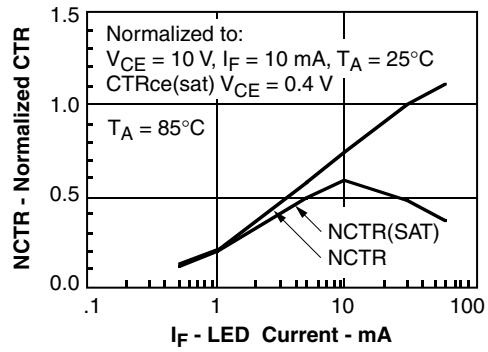


Figure 6. Collector-emitter current versus temperature and LED current

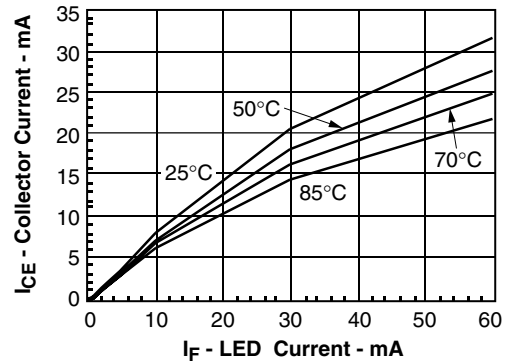


Figure 7. Collector-emitter leakage current versus temperature

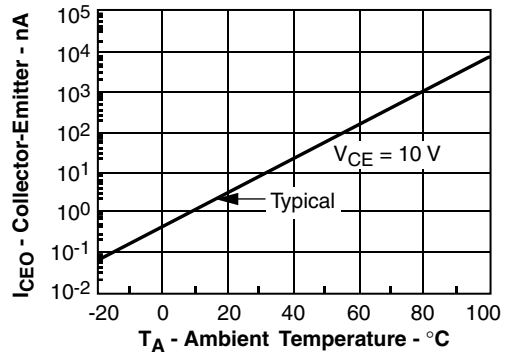


Figure 8. Normalized CTR_{cb} versus LED current and temperature

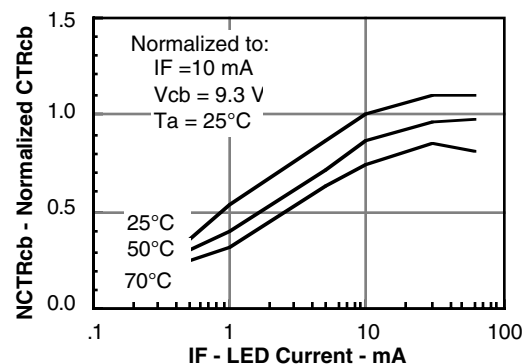


Figure 9. Collector base photocurrent versus LED current

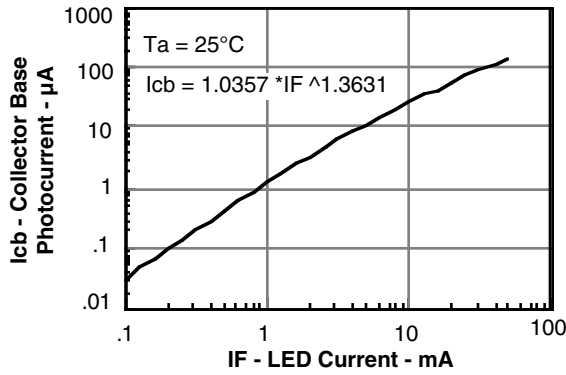


Figure 10. Normalized photocurrent versus I_F and temperature

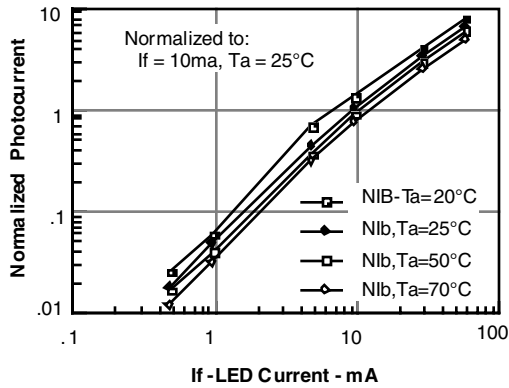


Figure 11. Normalized saturated HFE versus base current and temperature

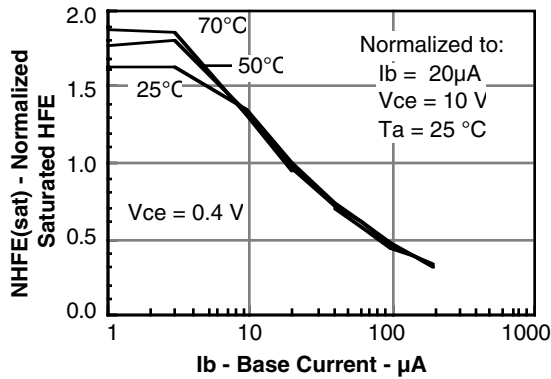


Figure 12. Propagation delay versus collector load resistor

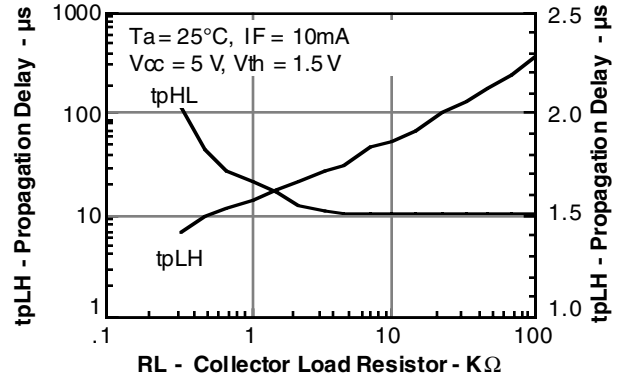


Figure 13. Normalized non-saturated and saturated CTR_{ce} versus LED current

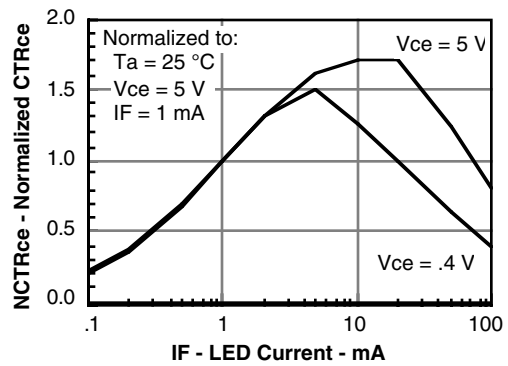


Figure 14. Normalized non-saturated HFE versus base current and temperature

